18Mb Pipelined QDR™II SRAM Burst of 2

Advance Information
IDT71P72204
IDT71P72104
IDT71P72804
IDT71P72604

Features

- ◆ 18Mb Density (2Mx8, 2Mx9, 1Mx18, 512kx36)
- ◆ Separate, Independent Read and Write Data Ports
    - Supports concurrent transactions
- ◆ Dual Echo Clock Output
- ◆ 2-Word Burst on all SRAM accesses
- ◆ DDR (Double Data Rate) Multiplexed Address Bus
    - One Read and One Write request per clock cycle
- ◆ DDR (Double Data Rate) Data Buses
    - Two word burst data per clock on each port
    - Four word transfers per clock cycle (2 word bursts on 2 ports)
- ◆ Depth expansion through Control Logic
- ◆ HSTL (1.5V) inputs that can be scaled to receive signals from 1.4V to 1.9V.
- ◆ Scalable output drivers
    - Can drive HSTL, 1.8V TTL or any voltage level from 1.4V to 1.9V.
    - Output Impedance adjustable from 35 ohms to 70 ohms
- ◆ 1.8V Core Voltage (VDD)
- ◆ 165-ball, 1.0mm pitch, 15mm x 17mm fBGA Package
- ◆ JTAG Interface

Description

The IDT QDRII™ Burst of two SRAMs are high-speed synchronous memories with independent, double-data-rate (DDR), read and write data ports. This scheme allows simultaneous read and write access for the maximum device throughput, with two data items passed with each read or write. Four data word transfers occur per clock cycle, providing quad-data-rate (QDR) performance. Comparing this with standard SRAM common I/O (CIO), single data rate (SDR) devices, a four to one increase in data access is achieved at equivalent clock speeds. Considering that QDRII allows clock speeds in excess of standard SRAM devices, the throughput can be increased well beyond four to one in most applications.

Using independent ports for read and write data access, simplifies system design by eliminating the need for bi-directional buses. All buses associated with the QDRII are unidirectional and can be optimized for signal integrity at very high bus speeds. The QDRII has scalable output impedance on its data output bus and echo clocks, allowing the user to tune the bus for low noise and high performance.

The QDRII has a single DDR address bus with multiplexed read and write addresses. All read addresses are received on the first half of the clock cycle and all write addresses are received on the second half of the clock cycle. The read and write enables are received on the first half of the clock cycle. The byte and nibble write signals are received on both halves of the clock cycle simultaneously with the data they are controlling on the data input bus.

The QDRII has echo clocks, which provide the user with a clock

Functional Block Diagram

6109 drw 16
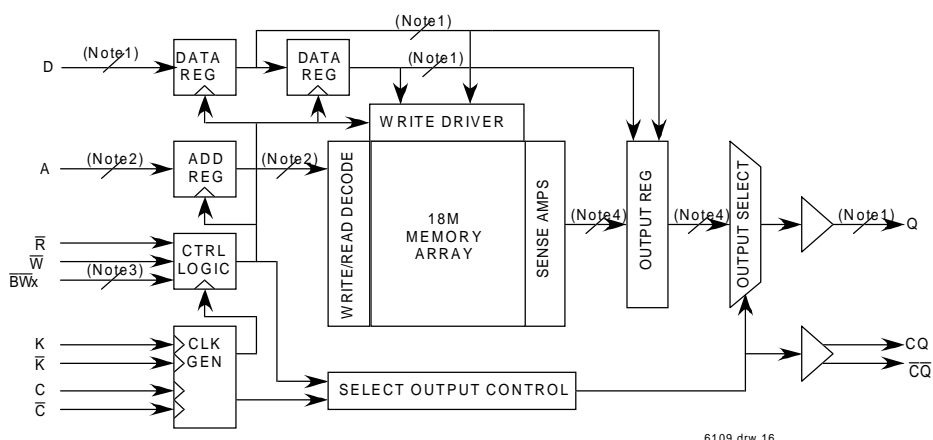
Notes
1) Represents 8 data signal lines for x8, 9 signal lines for x9, 18 signal lines for x18, and 36 signal lines for x36
2) Represents 20 address signal lines for x8 and x9, 19 address signal lines for x18, and 18 address signal lines for x36.
3) Represents 1 signal line for x9, 2 signal lines for x18, and four signal lines for x36. On x8 parts, the $\overline{BW}$ is a "nibble write" and there are 2 signal lines.
4) Represents 16 data signal lines for x8, 18 signal lines for x9, 36 signal lines for x18, and 72 signal lines for x36.

AUGUST 2003

1

that is precisely timed to the data output, and tuned with matching impedance and signal quality. The user can use the echo clock for downstream clocking of the data. Echo clocks eliminate the need for the user to produce alternate clocks with precise timing, positioning, and signal qualities to guarantee data capture. Since the echo clocks are generated by the same source that drives the data output, the relationship to the data is not significantly affected by voltage, temperature and process, as would be the case if the clock were generated by an outside source.

All interfaces of the QDRII SRAM are HSTL, allowing speeds beyond SRAM devices that use any form of TTL interface. The interface can be scaled to higher voltages (up to 1.9V) to interface with 1.8V systems if necessary. The device has a V_{DDQ} and a separate Vref, allowing the user to designate the interface operational voltage, independent of the device core voltage of 1.8V V_{DD}. The output impedance control allows the user to adjust the drive strength to adapt to a wide range of loads and transmission lines.

The device is capable of sustaining full bandwidth on both the input and output ports simultaneously. All data is in two word bursts, with addressing capability to the burst level.

Clocking

The QDRII SRAM has two sets of input clocks, namely the K, $\overline{K}$ clocks and the C, $\overline{C}$ clocks. In addition, the QDRII has an output "echo" clock, CQ, $\overline{CQ}$.

The K and $\overline{K}$ clocks are the primary device input clocks. The K clock is, used to clock in the control signals ($\overline{R}$, $\overline{W}$ and $\overline{BW}$x or $\overline{NW}$x), the read address, and the first word of the data burst during a write operation. The $\overline{K}$ clock is used to clock in the control signals ($\overline{BW}$x or $\overline{NW}$x), write address and the second word of the data burst during a write operation. The K and $\overline{K}$ clocks are also used internally by the SRAM. In the event that the user disables the C and $\overline{C}$ clocks, the K and $\overline{K}$ clocks will also be used to clock the data out of the output register and generate the echo clocks.

The C and $\overline{C}$ clocks may be used to clock the data out of the output register during read operations and to generate the echo clocks. C and $\overline{C}$ must be presented to the SRAM within the timing tolerances. The output data from the QDRII will be closely aligned to the C and $\overline{C}$ input, through the use of an internal DLL. When C is presented to the QDRII SRAM, the DLL will have already internally clocked the data to arrive at the device output simultaneously with the arrival of the C clock. The $\overline{C}$ and second data item of the burst will also correspond.

Single Clock Mode

The QDRII SRAM may be operated with a single clock pair. C and $\overline{C}$ may be disabled by tying both signals high, forcing the outputs and echo clocks to be controlled instead by the K and $\overline{K}$ clocks.

DLL Operation

The DLL in the output structure of the QDRII SRAM can be used to closely align the incoming clocks C and $\overline{C}$ with the output of the data, generating very tight tolerances between the two. The user may disable the DLL by holding $\overline{Doff}$ low. With the DLL off, the C and $\overline{C}$ (or K and $\overline{K}$ if C and $\overline{C}$ are not used) will directly clock the output register of the SRAM. With the DLL off, there will be a propagation delay from the time the clock enters the device until the data appears at the output.

Echo Clock

The echo clocks, CQ and $\overline{CQ}$, are generated by the C and $\overline{C}$ clocks (or K, $\overline{K}$ if C, $\overline{C}$ are disabled). The rising edge of C generates the rising edge of CQ, and the falling edge of $\overline{CQ}$. The rising edge of $\overline{C}$ generates the rising edge of $\overline{CQ}$ and the falling edge of CQ. This scheme improves the correlation of the rising and falling edges of the echo clock and will improve the duty cycle of the individual signals.

The echo clock is very closely aligned with the data, guaranteeing that the echo clock will remain closely correlated with the data, within the tolerances designated.

Read and Write Operations

QDRII devices internally store the two words of the burst as a single, wide word and will retain their order in the burst. There is no ability to address to the single word level or reverse the burst order; however, the byte and nibble write signals can be used to prevent writing any individual bytes, or combined to prevent writing one word of the burst.

Read operations are initiated by holding the read port select ($\overline{R}$) low, and presenting the read address to the address port during the rising edge of K which will latch the address. The data will then be read and will appear at the device output at the designated time in correspondence with the C and $\overline{C}$ clocks.

Write operations are initiated by holding the write port select ($\overline{W}$) low and designating with the Byte Write inputs ($\overline{BW}$x) which bytes are to be written (or $\overline{NW}$x on x8 devices). The first word of the data must also be present on the data input bus D[X:0]. Upon the rising edge of K the first word of the burst will be latched into the input register. After K has risen, and the designated hold times observed, the second half of the clock cycle is initiated by presenting the write address to the address bus A[X:0], the $\overline{BW}$x (or $\overline{NW}$x) inputs for the second data word of the burst, and the second data item of the burst to the data bus D[X:0]. Upon the rising edge of $\overline{K}$, the second word of the burst will be latched, along with the designated address. Both the first and second words of the burst will then be written into memory as designated by the address and byte write enables.

Output Enables

The QDRII SRAM automatically enables and disables the Q[X:0] outputs. When a valid read is in progress, and data is present at the output, the output will be enabled. If no valid data is present at the output (read not active), the output will be disabled (high impedance). The echo clocks will remain valid at all times and cannot be disabled or turned off. During power-up the Q outputs will come up in a high impedance state.

Programmable Impedance

An external resistor, RQ, must be connected between the ZQ pin on the SRAM and Vss to allow the SRAM to adjust its output drive impedance. The value of RQ must be 5X the value of the intended drive impedance of the SRAM. The allowable range of RQ to guarantee impedance matching with a tolerance of +/- 10% is between 175 ohms and 350 ohms, with V_{DDQ} = 1.5V. The output impedance is adjusted every 1024 clock cycles to correct for drifts in supply voltage and temperature. If the user wishes to drive the output impedance of the SRAM to it's lowest value, the ZQ pin may be tied to V_{DDQ}.

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Definitions

Symbol	Pin Function	Description
D[X:0]	Input Synchronous	Data input signals, sampled on the rising edge of K and $\overline{K}$ clocks during valid write operations 2M x 8 -- D[7:0] 2M x 9 -- D[8:0] 1M x 18 -- D[17:0] 512K x 36 -- D[35:0]
$\overline{BW}_0$, $\overline{BW}_1$ $\overline{BW}_2$, $\overline{BW}_3$	Input Synchronous	Byte Write Select 0, 1, 2, and 3 are active LOW. Sampled on the rising edge of the K and again on the rising edge of $\overline{K}$ clocks during write operations. Used to select which byte is written into the device during the current portion of the write operations. Bytes not written remain unaltered. All the byte writes are sampled on the same edge as the data. Deselecting a Byte Write Select will cause the corresponding byte of data to be ignored and not written in to the device. 2M x 9 -- $\overline{BW}_0$ controls D[8:0] 1M x 18 -- $\overline{BW}_0$ controls D[8:0] and $\overline{BW}_1$ controls D[17:9] 512K x 36 -- $\overline{BW}_0$ controls D[8:0], $\overline{BW}_1$ controls D[17:9], $\overline{BW}_2$ controls D[26:18] and $\overline{BW}_3$ controls D[35:27]
$\overline{NW0}$ $\overline{NW1}$	Input Synchronous	Nibble Write Select 0 and 1 are active LOW. Available only on x8 bit parts instead of Byte Write Selects. Sampled on the rising edge of the K and $\overline{K}$ clocks during write operations. Used to select which nibble is written into the device during the current portion of the write operations. Nibbles not written remain unaltered. All the nibble writes are sampled on the same edge as the data. Deselecting a Nibble Write Select will cause the corresponding nibble of data to be ignored and not written in to the device.
A	Input Synchronous	Address Inputs. Read addresses are sampled on the rising edge of K clock during active read operations. Write addresses are sampled on the rising edge of $\overline{K}$ clock during active write operations. These address inputs are multiplxed, so that both a read and write operation can occur on the same clock cycle. These inputs are ignored when the appropriate port is deselected.
Q[X:0]	Output Synchronous	Data Output signals. These pins drive out the requested data during a Read operation. Valid data is driven out on the rising edge of both the C and $\overline{C}$ clocks during Read operations or K and $\overline{K}$ when operating in single clock mode. When the Read port is deselected, Q[X:0] are automatically three-stated.
$\overline{W}$	Input Synchronous	Write Control Logic active Low. Sampled on the rising edge of the positive input clock (K). When asserted active, a write operation in initiated. Deasserting will deselect the Write port. Deselecting the Write port will cause D[X:0] to be ignored.
$\overline{R}$	Input Synchronous	Read Control Logic, active LOW. Sampled on the rising edge of Positive Input Clock (K). When active, a Read operation is initiated. Deasserting will cause the Read port to be deselected. When deselected, the pending access is allowed to complete and the output drivers are automatically three-stated following the next rising edge of the C clock. Each read access consists of a burst of two sequential transfer.
C	Input Clock	Positive Output Clock Input. C is used in conjunction with $\overline{C}$ to clock out the Read data from the device. C and $\overline{C}$ can be used together to deskew the flight times of various devices on the board back to the controller. See application example for further details.
$\overline{C}$	Input Clock	Negative Output Clock Input. $\overline{C}$ is used in conjunction with C to clock out the Read data from the device. C and $\overline{C}$ can be used together to deskew the flight times of various devices on the board back to the controller. See application example for further details.
K	Input Clock	Positive Input Clock Input. The rising edge of K is used to capture synchronous inputs to the device and to drive out data through Q[X:0] when in single clock mode. All accesses are initiated on the rising edge of K.
$\overline{K}$	Input Clock	Negative Input Clock Input. $\overline{K}$ is used to capture synchronous inputs being presented to the device and to drive out data through Q[X:0] when in single clock mode.
CQ, $\overline{CQ}$	Output Clock	Synchronous Echo clock outputs. The rising edges of these outputs are tightly matched to the synchronous data outputs and can be used as a data valid indication. These signals are free running and do not stop when the output data is tri-stated.
ZQ	Input	Output Impedance Matching Input. This input is used to tune the device outputs to the system data bus impedance. Q[X:0] output impedance is set to 0.2 x RQ, where RQ is a resistor connected between ZQ and ground. Alternately, this pin can be connected directly to V_{DDQ}, which enables the minimum impedance mode. This pin cannot be connected directly to GND or left unconnected.

6109 tbl 02a

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Definitions continued

Symbol	Pin Function	Description
$\overline{Doff}$	Input	DLL Turn Off. When low this input will turn off the DLL inside the device. The AC timings with the DLL turned off will be different from those listed in this data sheet. There will be an increased propagation delay from the incidence of C and $\overline{C}$ to Q, or K and $\overline{K}$ to Q as configured. The propagation delay is not a tested parameter, but will be similar to the propagation delay of other SRAM devices in this speed grade.
TDO	Output	TDO pin for JTAG
TCK	Input	TCK pin for JTAG.
TDI	Input	TDI pin for JTAG. An internal resistor will pull TDI to V_{DD} when the pin is unconnected.
TMS	Input	TMS pin for JTAG. An internal resistor will pull TMS to V_{DD} when the pin is unconnected.
NC		No connects inside the package. Can be tied to any voltage level
V_{REF}	Input Reference	Reference Voltage input. Static input used to set the reference level for HSTL inputs and Outputs as well as AC measurement points.
V_{DD}	Power Supply	Power supply inputs to the core of the device. Should be connected to a 1.8V power supply.
V_{SS}	Ground	Ground for the device. Should be connected to ground of the system.
V_{DDQ}	Power Supply	Power supply for the outputs of the device. Should be connected to a 1.5V power supply for HSTL or scaled to the desired output voltage.

6109 tbl 02b

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Configuration 2M x 8

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	Vss	A	$\overline{W}$	$\overline{NW}_1$	$\overline{K}$	NC	$\overline{R}$	A	Vss	CQ
B	NC	NC	NC	A	NC	K	$\overline{NW}_0$	A	NC	NC	Q3
C	NC	NC	NC	Vss	A	A	A	Vss	NC	NC	D3
D	NC	D4	NC	Vss	Vss	Vss	Vss	Vss	NC	NC	NC
E	NC	NC	Q4	VDDQ	Vss	Vss	Vss	VDDQ	NC	D2	Q2
F	NC	NC	NC	VDDQ	VDD	Vss	VDD	VDDQ	NC	NC	NC
G	NC	D5	Q5	VDDQ	VDD	Vss	VDD	VDDQ	NC	NC	NC
H	$\overline{Doff}$	VREF	VDDQ	VDDQ	VDD	Vss	VDD	VDDQ	VDDQ	VREF	ZQ
J	NC	NC	NC	VDDQ	VDD	Vss	VDD	VDDQ	NC	Q1	D1
K	NC	NC	NC	VDDQ	VDD	Vss	VDD	VDDQ	NC	NC	NC
L	NC	Q6	D6	VDDQ	Vss	Vss	Vss	VDDQ	NC	NC	Q0
M	NC	NC	NC	Vss	Vss	Vss	Vss	Vss	NC	NC	D0
N	NC	D7	NC	Vss	A	A	A	Vss	NC	NC	NC
P	NC	NC	Q7	A	A	C	A	A	NC	NC	NC
R	TDO	TCK	A	A	A	$\overline{C}$	A	A	A	TMS	TDI

6109 tbl 12

165-ball FBGA Pinout
TOP VIEW

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Configuration 2M x 9

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	V_{SS}	A	$\overline{W}$	NC	$\overline{K}$	NC	$\overline{R}$	A	V_{SS}	CQ
B	NC	NC	NC	A	NC	K	$\overline{BW}$	A	NC	NC	Q3
C	NC	NC	NC	V_{SS}	A	A	A	V_{SS}	NC	NC	D3
D	NC	D4	NC	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	NC	NC
E	NC	NC	Q4	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	D2	Q2
F	NC	NC	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	NC
G	NC	D5	Q5	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	NC
H	$\overline{Doff}$	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	NC	NC	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	Q1	D1
K	NC	NC	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	NC
L	NC	Q6	D6	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	NC	Q0
M	NC	NC	NC	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	NC	D0
N	NC	D7	NC	V_{SS}	A	A	A	V_{SS}	NC	NC	NC
P	NC	NC	Q7	A	A	C	A	A	NC	D8	Q8
R	TDO	TCK	A	A	A	$\overline{C}$	A	A	A	TMS	TDI

6109 tbl 12a

165-ball FBGA Pinout
TOP VIEW

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Configuration 1M x 18

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	V_{SS}	NC	$\overline{W}$	$\overline{BW1}$	$\overline{K}$	NC	$\overline{R}$	A	V_{SS}	CQ
B	NC	Q_9	D_9	A	NC	K	$\overline{BW0}$	A	NC	NC	Q_8
C	NC	NC	D_{10}	V_{SS}	A	A	A	V_{SS}	NC	Q_7	D_8
D	NC	D_{11}	Q_{10}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	NC	D_7
E	NC	NC	Q_{11}	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	D_6	Q_6
F	NC	Q_{12}	D_{12}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	Q_5
G	NC	D_{13}	Q_{13}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	NC	D_5
H	$\overline{Doff}$	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	NC	NC	D_{14}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	Q_4	D_4
K	NC	NC	Q_{14}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	NC	D_3	Q_3
L	NC	Q_{15}	D_{15}	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC	NC	Q_2
M	NC	NC	D_{16}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	NC	Q_1	D_2
N	NC	D_{17}	Q_{16}	V_{SS}	A	A	A	V_{SS}	NC	NC	D_1
P	NC	NC	Q_{17}	A	A	C	A	A	NC	D_0	Q_0
R	TDO	TCK	A	A	A	$\overline{C}$	A	A	A	TMS	TDI

6109 tbl 12b

165-ball FBGA Pinout
TOP VIEW

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Pin Configuration 512K x 36

	1	2	3	4	5	6	7	8	9	10	11
A	$\overline{CQ}$	V_{SS}	NC	$\overline{W}$	$\overline{BW}_2$	$\overline{K}$	$\overline{BW}_1$	$\overline{R}$	NC	V_{SS}	CQ
B	Q_{27}	Q_{18}	D_{18}	A	$\overline{BW}_3$	K	$\overline{BW}_0$	A	D_{17}	Q_{17}	Q_8
C	D_{27}	Q_{28}	D_{19}	V_{SS}	A	A	A	V_{SS}	D_{16}	Q_7	D_8
D	D_{28}	D_{20}	Q_{19}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	Q_{16}	D_{15}	D_7
E	Q_{29}	D_{29}	Q_{20}	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	Q_{15}	D_6	Q_6
F	Q_{30}	Q_{21}	D_{21}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D_{14}	Q_{14}	Q_5
G	D_{30}	Q_{22}	Q_{22}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q_{13}	D_{13}	D_5
H	$\overline{D_{off}}$	V_{REF}	V_{DDQ}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	V_{DDQ}	V_{REF}	ZQ
J	D_{31}	Q_{31}	D_{23}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	D_{12}	Q_4	D_4
K	Q_{32}	D_{32}	Q_{23}	V_{DDQ}	V_{DD}	V_{SS}	V_{DD}	V_{DDQ}	Q_{12}	D_3	Q_3
L	Q_{33}	Q_{24}	D_{24}	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	D_{11}	Q_{11}	Q_2
M	D_{33}	Q_{34}	D_{25}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	D_{10}	Q_1	D_2
N	D_{34}	D_{26}	Q_{25}	V_{SS}	A	A	A	V_{SS}	Q_{10}	D_9	D_1
P	Q_{35}	D_{35}	Q_{26}	A	A	C	A	A	Q_9	D_0	Q_0
R	TDO	TCK	A	A	A	$\overline{C}$	A	A	A	TMS	TDI

6109 tbl 12c

165-ball FBGA Pinout
TOP VIEW

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Absolute Maximum Ratings[1]

Symbol	Rating	Value	Unit
V_{TERM}	Supply Voltage on V_{DD} with Respect to GND	−0.5 to +2.9	V
V_{TERM}	Supply Voltage on V_{DDQ} with Respect to GND	−0.5 to V_{DD}+0.3	V
V_{TERM}	Voltage on Input, Output and I/O terminals with respect to GND	−0.5 to V_{DDQ}+0.3	V
T_{BIAS}	Temperature Under Bias	−55 to +125	°C
T_{STG}	Storage Temperature	−65 to +150	°C
I_{OUT}	Continuous Current into Outputs	± 20	mA

6109 tbl 05

NOTE:
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Capacitance (TA = +25°C, f = 1.0MHz)[1]

Symbol	Parameter	Conditions	Max.	Unit
C_{IN}	Input Capacitance	V_{DD} = 1.8V V_{DDQ} = 1.5V	5	pF
C_{CLK}	Clock Input Capacitance		6	pF
C_O	Output Capacitance		7	pF

6109 tbl 06

NOTE:
1. Tested at characterization and retested after any design or process change that may affect these parameters.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Typ.	Max.	Unit
V_{DD}	Power Supply Voltage	1.7	1.8	1.9	V
V_{DDQ}	I/O Supply Voltage	1.4	1.5	1.9	V
V_{SS}	Ground	0	0	0	V
V_{REF}	Input Reference Voltage	-	$V_{DDQ}/2$	-	V
V_{IH}	Input High Voltage	V_{REF}+0.1	–	V_{DDQ}+0.3	V
V_{IL}	Input Low Voltage	−0.3	–	V_{REF}−0.1	V
T_A	Ambient Temperature	0	25	+70	°C

6109 tbl 04

Write Descriptions[1,2]

Signal	$\overline{BW}_0$	$\overline{BW}_1$	$\overline{BW}_2$	$\overline{BW}_3$	$\overline{NW}_0$	$\overline{NW}_1$
Write Byte 0	L	X	X	X	X	X
Write Byte 1	X	L	X	X	X	X
Write Byte 2	X	X	L	X	X	X
Write Byte 3	X	X	X	L	X	X
Write Nibble 0	X	X	X	X	L	X
Write Nibble 1	X	X	X	X	X	L

6109 tbl 09

Notes:
1) All byte write ($\overline{BW}$x) and nibble write ($\overline{NW}$x) signals are sampled on the rising edge of K and again on $\overline{K}$. The data that is present on the data bus in the designated byte/nibble will be latched into the input if the corresponding $\overline{BW}$x or $\overline{NW}$x is held low. The rising edge of K will sample the first byte/nibble of the two word burst and the rising edge of $\overline{K}$ will sample the second byte/nibble of the two word burst.
2) The availability of the $\overline{BW}$x or $\overline{NW}$x on designated devices is described in the pin description table.
3) The QDRII Burst of two SRAM has data forwarding. A read request that is initiated on the same cycle as a write request to the same address will produce the newly written data in response to the read request.

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Application Example
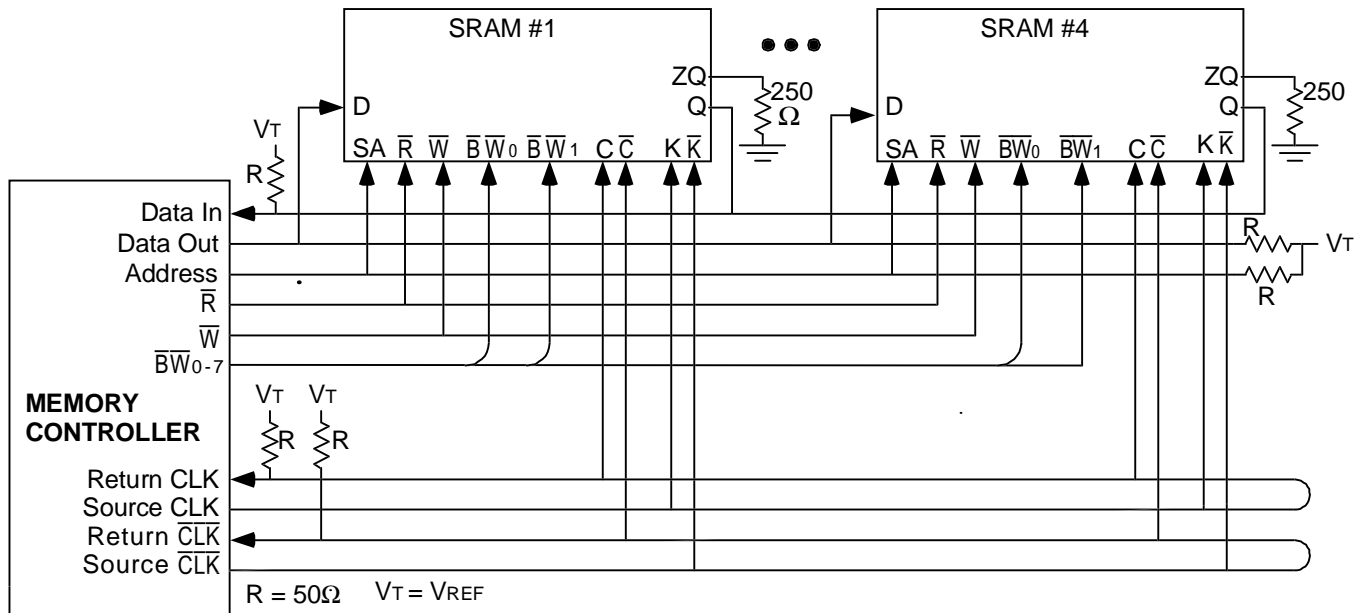
6109 drw 20

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range $(V_{DD} = 1.8 \pm 100mV, V_{DDQ} = 1.4V$ to $1.9V)$
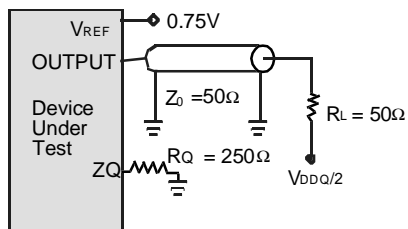
Parameter	Symbol	Test Conditions		Min	Max	Unit	Note
Input Leakage Current	I_{IL}	V_{DD} = Max V_{IN} = VSS to V_{DDQ}		-10	+10	µA	
Output Leakage Current	I_{OL}	Output Disabled		-10	+10	µA	
Operating Current (x36,x18,x9,x8) DDR	I_{DD}	V_{DD} = Max, I_{OUT} = 0mA Cycle Time $\geq$ t_{KHKH} Min	250MHz	-	TBD	mA	1,5
			200MHz	-	TBD		
			167MHz	-	TBD		
			133MHz	-	TBD		
Standby Current (NOP): DDR	I_{SB1}	Device Deselected, I_{OUT} = 0mA, f=Max, All Inputs $\leq$0.2V or > VDD -0.2V	250MHz	-	TBD	mA	1,6
			200MHz	-	TBD		
			167MHz	-	TBD		
			133MHz	-	TBD		
Output High Voltage	V_{OH1}	See Note 2		V_{DDQ}/2-0.12	V_{DDQ}/2+0.12	V	2,7
Output Low Voltage	V_{OL1}	See Note 3		V_{DDQ}/2-0.12	V_{DDQ}/2+0.12	V	3,7
Output High Voltage	V_{OH2}	I_{OH} = -0.1mA		V_{DDQ}-0.2	V_{DDQ}	V	4
Output Low Voltage	V_{OL2}	I_{OL} = 0.1mA		VSS	0.2	V	4
Input Low Voltage	V_{IL}			-0.3	V_{REF}-0.1	V	8,9
Input High Voltage	V_{IH}			V_{REF}+0.1	V_{DDQ}+0.3	V	8,10

6109 tbl 10c

Notes:

1. Minimum cycle. I_{OUT} = 0mA.
2. I_{OH} = -(V_{DDQ}/2)/(RQ/5) for 175Ω $\leq$ RQ < 350Ω.
3. I_{OL} = (V_{DDQ}/2)/(RQ/5) for 175Ω $\leq$ RQ < 350Ω.
4. Minimum Impedance Mode when ZQ pin is connected to V_{DDQ}.
5. Operating Current is calculated with 50% read cycles and 50% write cycles.
6. Standby Current is only after all pending read and write burst operations are completed.
7. Programmable Impedance Mode.
8. These are DC test criteria. DC design criteria is V_{REF} $\pm$ 50mV. The AC V_{IH}/V_{IL} levels are defined separately for measuring timing parameters.
9. V_{IL} (Min) DC = -0.3V, V_{IL} (Min) AC = -1.5V (pulse width $\leq$3ns).
10. V_{IH} (Max) DC = V_{DDQ}+0.3, V_{IH} (Max) AC = V_{DDQ}+0.85V (pulse width$\leq$3ns)

AC Test Loads

6109 drw 04

AC Test Conditions

Parameter	Symbol	Value	Unit
Core Power Supply Voltage	V_{DD}	1.7-1.9	V
Output Power Supply Voltage	V_{DDQ}	1.4-1.9	V
Input High/Low Level	V_{IH}/V_{IL}	1.25/0.25	V
Input Reference Level	VREF	0.75	V
Input Rise/Fall Time	TR/TF	0.6/0.6	ns
Output Timing Reference Level	V_{DDQ}/2		V

6109 tbl 11a

NOTE:

1. Parameters are tested with RQ=250Ω
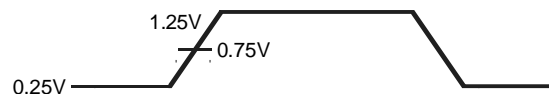
6109 drw 06

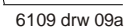## AC Electrical Characteristics (V_{DD} = 1.8 ± 100mV, V_{DDQ} = 1.4V to 1.9V)[3]

Symbol	Parameter	250MHz		200MHz		167MHz		133MHz		Unit	Notes
		Min.	Max	Min.	Max	Min.	Max	Min	Max		
Clock Parameters											
tKHKH	Average clock cycle time (K,$\overline{K}$,C,C)	4.00	5.25	5.00	6.30	6.00	7.88	7.50	8.40	ns	
tKC var	Clock Phase Jitter (K,$\overline{K}$,C,$\overline{C}$)	-	0.20	-	0.20	-	0.20	-	0.20	ns	5
tKHKL	Clock High Time (K,$\overline{K}$,C,$\overline{C}$)	1.60	-	2.00	-	2.40	-	3.00	-	ns	
tKLKH	Clock LOW Time (K,$\overline{K}$,C,$\overline{C}$)	1.60	-	2.00	-	2.40	-	3.00	-	ns	
tKH$\overline{K}$H	Clock to $\overline{clock}$ (K→$\overline{K}$,C→$\overline{C}$)	1.80	-	2.20	-	2.70	-	3.38	-	ns	
t$\overline{K}$HKH	Clock to $\overline{clock}$ ($\overline{K}$→K,$\overline{C}$→C)	1.80	-	2.20	-	2.70	-	3.38	-	ns	
tKHCH	Clock to data clock (K→C,$\overline{K}$→$\overline{C}$)	0.00	1.80	0.00	2.30	0.00	2.80	0.00	3.55	ns	
tKC lock	DLL lock time (K, C)	1024	-	1024	-	1024	-	1024	-	cycles	6
tKC reset	K static to DLL reset	30	-	30	-	30	-	30	-	ns	
Output Parameters											
tCHQV	C,$\overline{C}$ HIGH to output valid	-	0.45	-	0.45	-	0.50	-	0.50	ns	3
tCHQX	C,$\overline{C}$ HIGH to output hold	-0.45	-	-0.45	-	-0.50	-	-0.50	-	ns	3
tCHCQV	C,$\overline{C}$ HIGH to echo clock valid	-	0.45	-	0.45	-	0.50	-	0.50	ns	
tCHCQX	C,$\overline{C}$ HIGH to echo clock hold	-0.45	-	-0.45	-	-0.50	-	-0.50	-	ns	
tCQHQV	CQ,$\overline{CQ}$ HIGH to output valid	-	0.30	-	0.35	-	0.40	-	0.40	ns	7
tCQHQX	CQ,$\overline{CQ}$ HIGH to output hold	-0.30	-	-0.35	-	-0.40	-	-0.40	-	ns	7
tCHQZ	$\overline{C}$ HIGH to output High-Z	-	0.45	-	0.45	-	0.50	-	0.50	ns	3
tCHQX1	$\overline{C}$ HIGH to output Low-Z	-0.45	-	-0.45	-	-0.50	-	-0.50	-	ns	3
Set-Up Times											
tAVKH	Address valid to K,$\overline{K}$ rising edge	0.40	-	0.40	-	0.50	-	0.50	-	ns	
tIVKH	Control inputs valid to K,$\overline{K}$ rising edge	0.40	-	0.40	-	0.50	-	0.50	-	ns	2
tDVKH	Date-in valid to K, $\overline{K}$ rising edge	0.40	-	0.40	-	0.50	-	0.50	-	ns	
Hold Times											
tKHAX	K,$\overline{K}$ rising edge to address hold	0.40	-	0.40	-	0.50	-	0.50	-	ns	
tKHIX	K,$\overline{K}$ rising edge to control inputs hold	0.40	-	0.40	-	0.50	-	0.50	-	ns	
tKHDX	K, $\overline{K}$ rising edge to data-in hold	0.40	-	0.40	-	0.50	-	0.50	-	ns	

6109 tbl 11

NOTES:
1. All address inputs must meet the specified setup and hold times for all latching clock edges.
2. Control signals are $\overline{R}$, $\overline{W}$,$\overline{BW}_0$,$\overline{BW}_1$ and ($\overline{NW}_0$,$\overline{NW}_1$, for x8) and ($\overline{BW}_2$,$\overline{BW}_3$ also for x36)
3. If C,$\overline{C}$ are tied high, K,$\overline{K}$ become the references for C,$\overline{C}$ timing parameters.
4. To avoid bus contention, at a given voltage and temperature tCHQX1 is bigger than tCHQZ.
   The specs as shown do not imply bus contention because tCHQX1 is a MIN parameter that is worst case at totally different test conditions
   (0°C, 1.9V) than tCHQZ, which is a MAX parameter (worst case at 70°C, 1.7V)
    It is not possible for two SRAMs on the same board to be at such different voltage and temperature.
5. Clock phase jitter is the variance from clock rising edge to the next expected clock rising edge.
6. V_{dd} slew rate must be less than 0.1V DC per 50 ns for DLL lock retention. DLL lock time begins once Vdd and input clock are stable.
7. Echo clock is very tightly controlled to data valid/data hold. By design, there is a ± 0.1 ns variation from echo clock to data. The data sheet
    parameters reflect tester guardbands and test setup variations.

**IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)**
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Timing Waveform of Combined Read and Write Cycles

6109 drw 09a

IEEE 1149.1 TEST ACCESS PORT AND BOUNDARY SCAN-JTAG

This part contains an IEEE standard 1149.1 Compatible Test Access Port (TAP). The package pads are monitored by the Serial Scan circuitry when in test mode. This is to support connectivity testing during manufacturing and system diagnostics. In conformance with IEEE 1149.1, the SRAM contains a TAP controller, Instruction register, Bypass Register and ID register. The TAP controller has a standard 16-state machine that resets internally upon power-up; therefore, the TRST signal is not required. It is possible to use this device without utilizing the TAP. To disable the TAP controller without interfacing with normal operation of the SRAM, TCK must be tied to V_{SS} to preclude a mid level input. TMS and TDI are designed so an undriven input will produce a response identical to the application of a logic 1, and may be left unconnected, but they may also be tied to V_{DD} through a register. TDO should be left unconnected.

JTAG Block Diagram

6109 drw 18
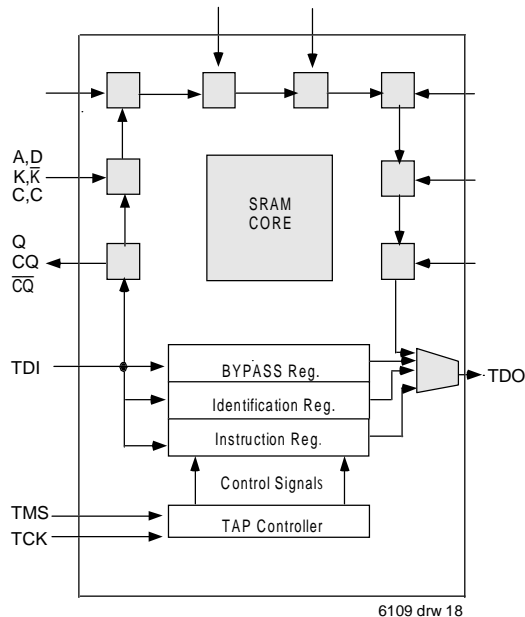
JTAG Instruction Coding

IR2	IR1	IR0	Instruction	TDO Output	Notes
0	0	0	EXTEST	Boundary Scan Register	
0	0	1	IDCODE	Identification register	2
0	1	0	SAMPLE-Z	Boundary Scan Register	1
0	1	1	RESERVED	Do Not Use	5
1	0	0	SAMPLE/PRELOAD	Boundary Scan register	4
1	0	1	RESERVED	Do Not Use	5
1	1	0	RESERVED	Do Not Use	5
1	1	1	BYPASS	Bypass Register	3

6109tbl 13

NOTE:

1. Places DQs in Hi-Z in order to sample all input data regardless of other SRAM inputs.
2. TDI is sampled as an input to the first ID register to allow for the serial shift of the external TDI data.
3. Bypass register is initiated to Vss when BYPASS instruction is invoked. The Bypass Register also holds serially loaded TDI when exiting the Shift DR states.
4. SAMPLE instruction does not place Qs in Hi-Z.
5. This instruction is reserved for future use.

TAP Controller State Diagram

6109 drw 17

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range
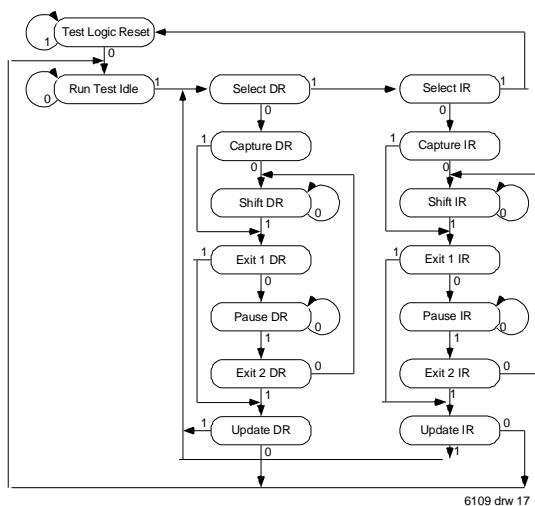
Scan Register Definition

Part	Instruction Register	Bypass Register	ID Register	Boundary Scan
512Kx36	3 bits	1 bit	32 bits	109 bits
1Mx18	3 bits	1 bit	32 bits	109 bits
2Mx8/x9	3 bits	1 bit	32 bits	109 bits

6109 tbl 14

Identification Register Definitions

INSTRUCTION FIELD	ALL DEVICES	DESCRIPTION	PART NUMBER
Revision Number (31:29)	000	Revision Number	
Device ID (28:12)	0010 0100 0100 0010 0100 0101 0010 0100 0110 0010 0100 0111	512Kx36　　　　QDRII Burst of 2 1Mx18 2Mx9 2Mx8	71P72604S 71P72804S 71P72104S 71P72204S
IDT JEDEC ID CODE (11:1)	0x33	Allows unique identification of SRAM vendor.	
ID Register Presence Indicator (0)	1	Indicates the presence of an ID register.	

6109 tbl 15

Boundary Scan Exit Order

ORDER	PIN ID
1	6R
2	6P
3	6N
4	7P
5	7N
6	7R
7	8R
8	8P
9	9R
10	11P
11	10P
12	10N
13	9P
14	10M
15	11N
16	9M
17	9N
18	11L
19	11M
20	9L
21	10L
22	11K
23	10K
24	9J
25	9K
26	10J
27	11J
28	11H
29	10G
30	9G
31	11F
32	11G
33	9F
34	10F
35	11E
36	10E

6109 tbl 16

ORDER	PIN ID
37	10D
38	9E
39	10C
40	11D
41	9C
42	9D
43	11B
44	11C
45	9B
46	10B
47	11A
48	10A
49	9A
50	8B
51	7C
52	6C
53	8A
54	7A
55	7B
56	6B
57	6A
58	5B
59	5A
60	4A
61	5C
62	4B
63	3A
64	Vss
65	1A
66	2B
67	3B
68	1C
69	1B
70	3D
71	3C
72	1D

6109 tbl 17

ORDER	PIN ID
73	2C
74	3E
75	2D
76	2E
77	1E
78	2F
79	3F
80	1G
81	1F
82	3G
83	2G
84	1H
85	1J
86	2J
87	3K
88	3J
89	2K
90	1K
91	2L
92	3L
93	1M
94	1L
95	3N
96	3M
97	1N
98	2M
99	3P
100	2N
101	2P
102	1P
103	3R
104	4R
105	4P
106	5P
107	5N
108	5R

6109 tbl 18

JTAG DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit	Note
Output Power Supply	V_{DDQ}	1.4	-	1.9	V	
Power Supply Voltage	V_{DD}	1.7	1.8	1.9	V	
Input High Level	V_{IH}	1.3	-	$V_{DD}+0.3$	V	
Input Low Level	V_{IL}	-0.3	-	0.5	V	
Output High Voltage (I_{OH} = -1mA)	V_{OH}	V_{DDQ} - 0.2	-	V_{DD}	V	1
Output Low Voltage (I_{OL} = 1mA)	V_{OL}	V_{SS}	-	0.2	V	1

Note: 1. ZQ = VDDQ2

6109 tbl 19

JTAG AC Test Conditions

Parameter	Symbol	Min	Unit	Note
Input High/Low Level	V_{IH}/V_{IL}	1.3/0.5	V	
Input Rise/Fall Time	TR/TF	1.0/1.0	ns	
Input and Output Timing Reference Level		$V_{DDQ}/2$	V	

6109 tbl 20

JTAG AC Characteristics

Parameter	Symbol	Min	Max	Unit	Note
TCK Cycle Time	t_{CHCH}	50	-	ns	
TCK High Pulse Width	t_{CHCL}	20	-	ns	
TCK Low Pulse Width	t_{CLCH}	20	-	ns	
TMS Input Setup Time	t_{MVCH}	5	-	ns	
TMS Input Hold Time	t_{CHMX}	5	-	ns	
TDI Input Setup Time	t_{DVCH}	5	-	ns	
TDI Input Hold Time	t_{CHDX}	5	-	ns	
SRAM Input Setup Time	t_{SVCH}	5	-	ns	
SRAM Input Hold Time	t_{CHSX}	5	-	ns	
Clock Low to Output Valid	t_{CLQV}	0	10	ns	

6109 tbl.21

JTAG Timing Diagram

6109 drw 19

IDT71P72204 (2M x 8-Bit), 71P72104 (2M x 9-Bit), 71P72804 (1M x 18-Bit) 71P72604 (512K x 36-Bit)
18 Mb QDR II SRAM Burst of 2

Advance Information
Commercial Temperature Range

Package Diagram Outline for 165-Ball Fine Pitch Grid Array

(165 BALL SHOWN)

NOTES:

1. ALL DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M-1994

2. "e" REPRESENTS THE BASIC SOLDER BALL GRID PITCH

3. "M" REPRESENTS THE MAXIMUM SOLDER BALL MATRIX SIZE

4. "N" REPRESENTS THE BALLCOUNT NUMBER

5. DIMENSION "b" IS MEASURED AT THE MAXIMUM SOLDER BALL DIAMETER, PARALLEL TO PRIMARY DATUM -C-

6. SEATING PLANE AND PRIMARY DATUM -C- ARE DEFINED BY THE SPHERICAL CROWNS OF THE SOLDER BALLS

7. "A1" ID CORNER MUST BE IDENTIFIED BY CHAMFER, INK MARK, METALLIZED MARKING, INDENTATION OR OTHER FEATURE ON PACKAGE BODY

8. IF "A1" ID CORNER IS ON PACKAGE BODY, IT MUST BE LOCATED WITHIN THE ZONE INDICATED

9. ALL DIMENSIONS ARE IN MILLIMETERS

(165 BALL)

S Y M B O L	JEDEC VARIATION NOT YET REGISTERED			N O T E
	MIN	NOM	MAX	
A	–	–	1.20	
A1	.30	.35	.40	
A2	.78	.85	.92	
D	15.00 BSC			
E	13.00 BSC			
M	11 X 15			3
N	165			4
e	1.00 BSC			
b	.35	.45	.50	5
CENTER BALL MATRIX	N/A			

TITLE BQ PACKAGE OUTLINE 13.0 X 15.0 mm BODY FPBGA
DRAWING No. PSC-4086 REV 00

Ordering Information

```
IDT    71P72XXX    S    XXX    BQ    X
       Device      Power Speed Package Process
       Type                            Temperature
                                       Range
```

Blank   Commercial (0°C to +70°C)

BQ   165 Fine Pitch Ball Grid Array (fBGA)

133 ⎤
167 ⎬   Clock Frequency in MegaHertz
200 ⎥
250 ⎦

IDT71P72204 2M x 8   QDR II SRAM
IDT71P72104 2M x 9   QDR II SRAM
IDT71P72804 1M x 18   QDR II SRAM
IDT71P72604 512K x 36 QDR II SRAM

6109 drw 15

Revision History

Revision	Date	Pages	Description
O	8/1/03	1-20	Initial Advance Information Data Sheet Release